## Integrated Molecular Beam Epitaxy System Model IMBE300-B

Epitaxial Growth Process with integrated monitoring, 2-D crystallography. composition and electronics band analysis in one UHV chamber.



Basic MBE System Configuration

## TECHNIQUES:

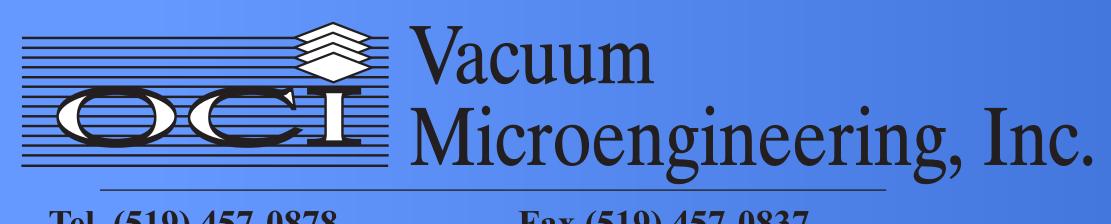
- LEED (Low Energy Electron Diffraction)
- AES (Auger Electron Spectroscopy)
- Thin Film Thickness Monitor
- 7 Deposition Sources

Available Ports:

- XPS (X-Ray Photoelectron Spectroscopy)
- RHEED (Reflection High Energy Electron Diffraction)
- TDS (Thermal Desorption Mass Spectroscopy)

## FEATURES:

- No need to transfer to another UHV chamber for analysis after film growth
  - Short switching time between deposition and surface science analysis
    - Load-lock with transfer arm and sample storage
    - Sample transfer compatibility with other systems: SPM and SEM



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